



Electrical characterization and polarization effect of the ultra fast heteroepitaxial diamond detectors







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Outlines

- Introduction
- Electrical and Electronic Properties
- Polarization and Memory Effects
- Conclusions

Diamond Detectors



Diamond







Diamond Detectors

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I-E characteristics DoI Detectors



I-E characteristics CVDD Detectors



Electrical Conductivity



Conduction Mechanism (SCLC)



type: sc CVD-DD, Dol DD contact: AI, Ti/Pt/Au, AI/DLC-Dia

theory of SCLC

$$I_{Child} = \frac{9}{8} \mu \varepsilon \frac{V^2}{d^3}$$
$$I_{TFL} = \frac{9}{8} \mu \varepsilon \theta \frac{V^2}{d^3}$$

Here,

 μ electronic mobility, V applied bias d thickness, ε dielectric constant

 $\theta = \frac{free_Carrier_Density}{Total_Carrier_Density}$

Effect of metalization on DoI



I-V characteristics at higher temp (>RT)

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E^{ac} of DoI & sc-CVDD



Charge Collection Efficiency (CCE) of CVDD



CCE of 3 different CVDDs

CCE of different DoI Detectors

The improvement of the CCE in Dol could be due the of the materials quality

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CCE and energy resolution of DoI



Polarization effect in DoI detectors



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Polarization effect in DoI detectors



Polarization effect in <u>different CVDD detectors</u>



polarization effect is more in pc-CVDD and Dol lies between pcand sc-CVDD detectors.

Polarization is effect are due the defects in the bulk of the diamonds

In term of the polarization effect the Dol behaves as 'quasi' sc CVDD detectors

CCE of 3 different CVDDs

Memory effect in DoI detectors



negative bias (1V/µm)

Dol 886-2 (320µm)

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Memory effect in DoI detectors



negative bias (1V/µm)

Dol 886-2 (320µm)

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Memory effect in DoI detectors



negative bias (2V/µm)

Dol 886-2 (320µm)

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Memory effect in different CVDD detectors



memory effect is more in pc-CVDD

In both bias condition the memory effect is similar in Dol detectors while this effect is varying in pc-diamond.

However in sc-CVDD detectors no such phenomenon is observed.

bias (>1V/µm)

CCE of 3 different CVDDs

Summaries

• Electrical (*I-V*) characteristics of scCVDD and Dol detectors are analyzed; the dark current of Dol samples is by one order magnitude lower than the current observed with scCVDD.

• The main dark current conductivity in scCVDD detector is SCLC and Dol is Space Charge Limited Conduction (SCLC) and E^{ac} is 0.37~0.39eV. While for Dol the *Eac* is (1.03~1.32)eV

• The CEE of Dol is improved with the new DOl samples $(11\% \rightarrow 93\%)$ also the energy resolution $(18\% \rightarrow 4\%)$

• The polarization effect is observed in Dol which lies between pcCVDD and scCVDD at positive bias while at neg. bias (V) the memory effect is visible.

Thank you for your attention